Positive photoresist

1. Clean the wafer with acetone, isopropanol, DI H_20, and blow dry with filtered N_2
2. Center the wafer on the chuck of the spin coater
3. Apply enough Shipley S1813 photoresist to cover the wafer completely, with special care not to have any bubbles in the resist.
4. Spin the wafer for 30 seconds at 3000RPM (acceleration at 300RPM/sec).
5. Bake the wafer for 10 minutes at 100°C (or 2 minutes at 130°C) on a hotplate
6. Align wafer on mask aligner, and expose to UV light for 8-10 seconds (at an exposure energy of 25-30 mJ/cm^2).

    Note: S1813, as a positive photoresist, is less sensitive to exposure dose than negative photoresists. As long as the baking is sufficient to cure the photoresist, the exposure dose simply needs to be above a minimum threshold to ensure accurate reproduction of features.

7. Develop in a bath of MF319 developer for 30-60 seconds
8. Rinse with DI H_2O to remove excess MF319 and blow dry with filtered N_2

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